145 GHz PHOTODETECTOR MODULE

Technical Background

High-speed photodetector modules are of interest for the development of next-generation optical communication links in datacom and telecom. Since these R&D links are always a step ahead in terms of symbol rates, photodetector modules with a RF bandwidth beyond state-of-the-art are needed at the receiver side. Furthermore, the high-speed performance of the photodetector modules makes them applicable in microwave photonics.

The photodetector chips inside the modules are based on mature InP technology and are fabricated at the wafer process line of HHI, having Telcordia and space-qualified processes. The modules are also packaged at Fraunhofer HHI facilities.

Features

- up to 145 GHz 3 dB-bandwidth
- detection of 200 GBAud amplitude modulated signals
- operation in C- and L-band
- integrated bias network
- low bias operation
- 0.8mm RF connector

Applications

- datacommunication
- telecommunication
- test- & measurement systems
- microwave photonics

AT A GLANCE

high-speed photodetector module for > 1 T/bs PAM datacom, telecom and microwave photonics applications
Technical Specifications

- wavelength: 1480nm - 1620nm
- 3 dB-bandwidth: up to 145 GHz
- low dark current: < 100 nA @ 3 V
- bias voltage: +2 V
- 0.8mm female RF connector
- RF output matched to 50 Ω
- optical input: FC/APC PM SMF fibre